

Non-Equilibrium Green's Function (NEGF) Simulation of nanowire MOSFET

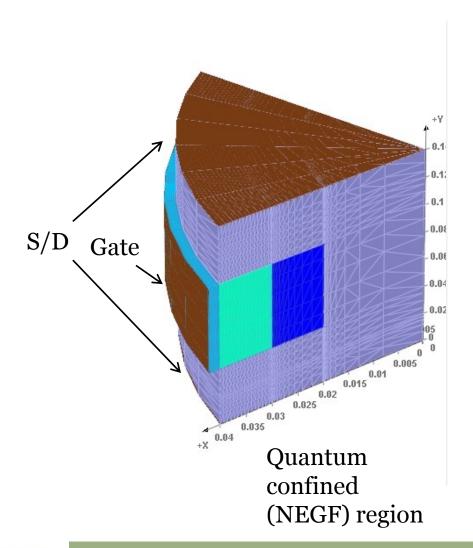


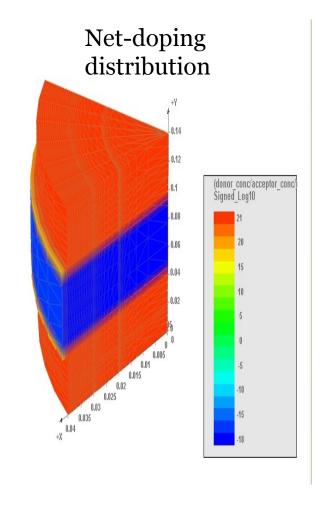
Advanced physical models of nanowire-MOSFET

- ➤ Use of cylindrical coordinate system to achieve maximum simulation efficiency.
- ➤ Hybrid approach with channel region using NEGF while all other regions using conventional drift-diffusion.
- ➤ Flexible choice of subbands to be included in NEGF quantum confinement and quantum ballistic transport.
- ➤ Self-consistent solution of NEGF equations with all other equations of drift-diffusion.

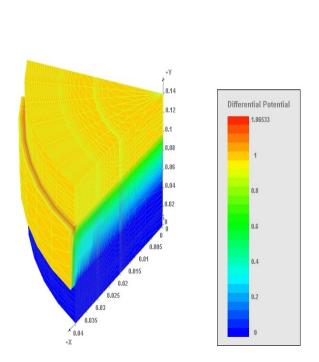




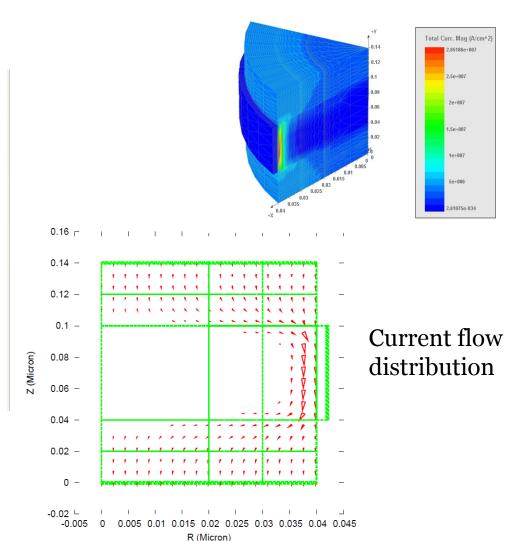




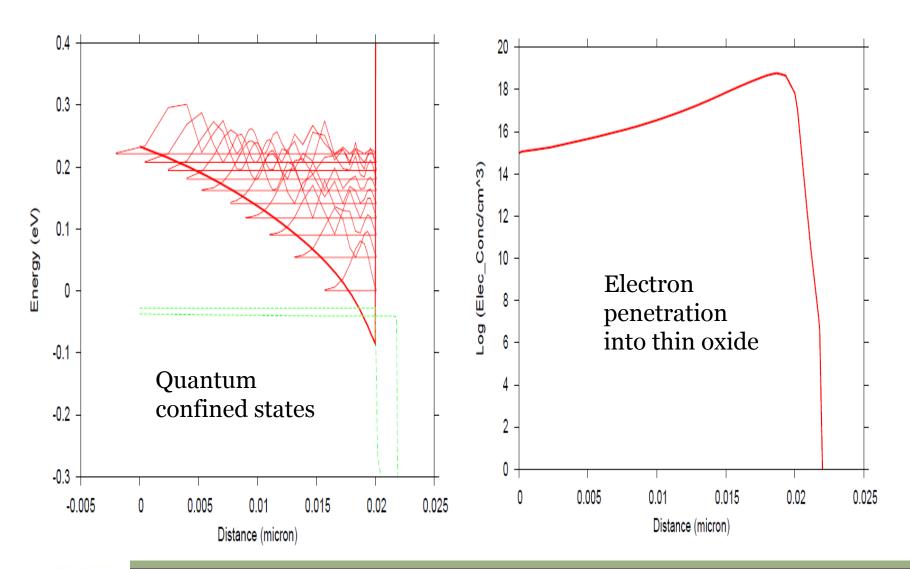




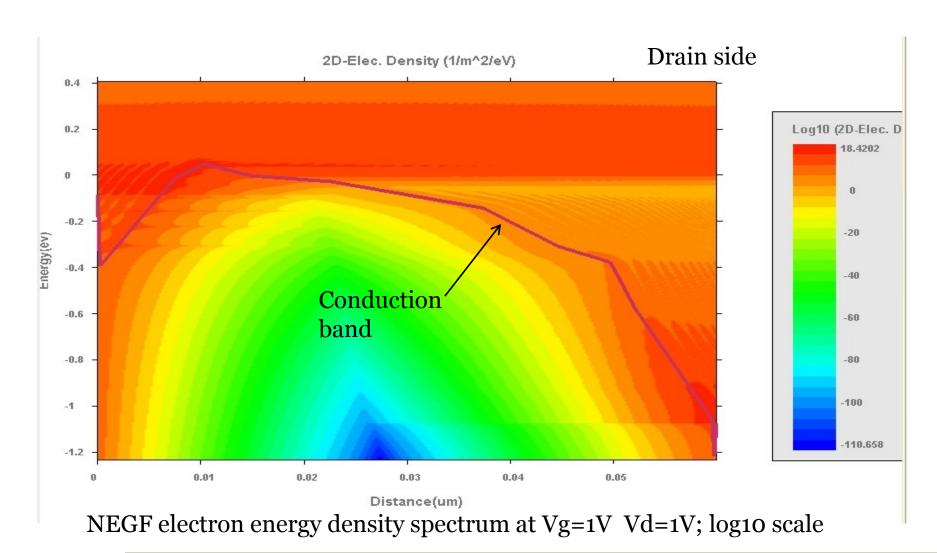
Differential potential/Bias distribution



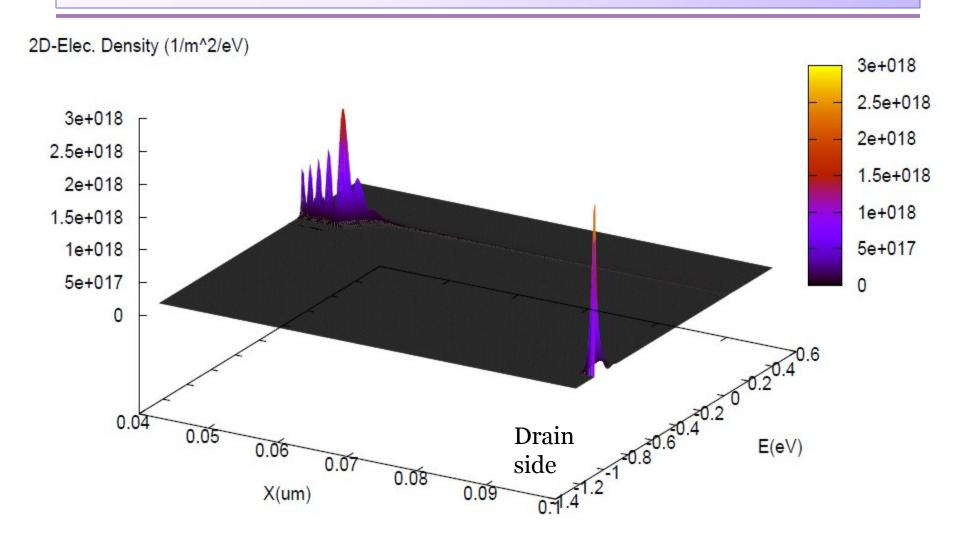






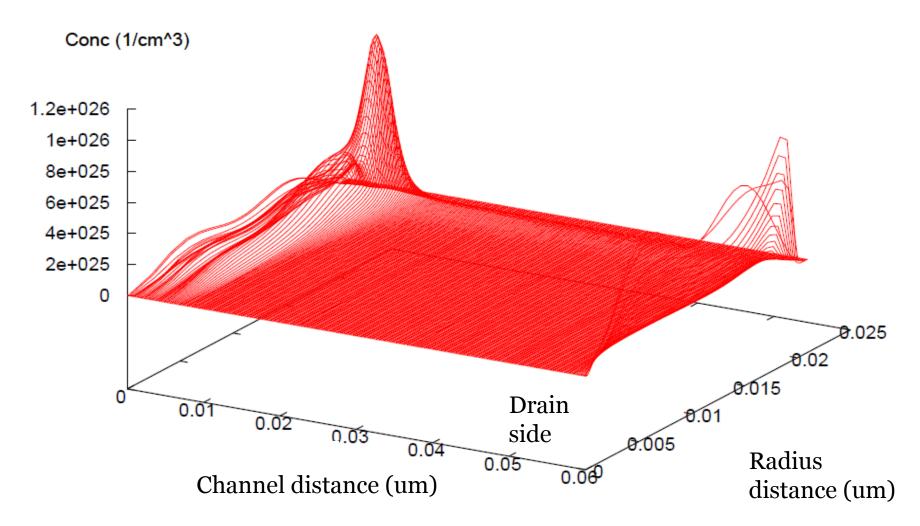






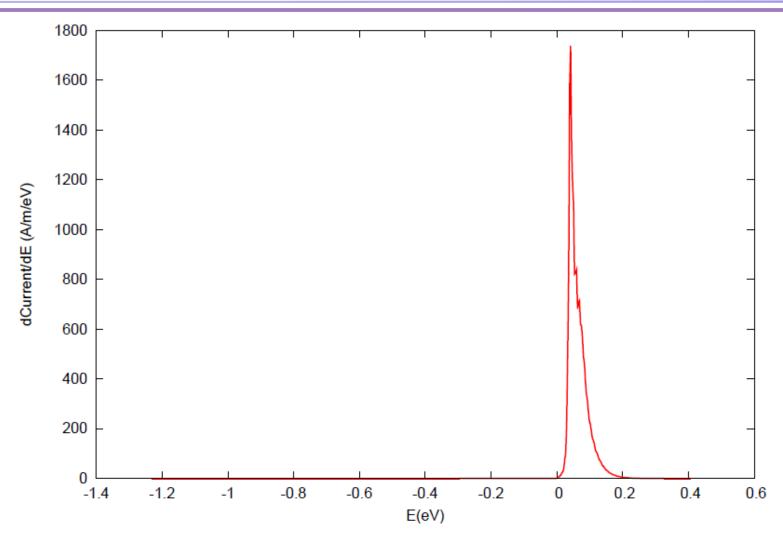
NEGF electron energy density spectrum at Vg=1V Vd=1V





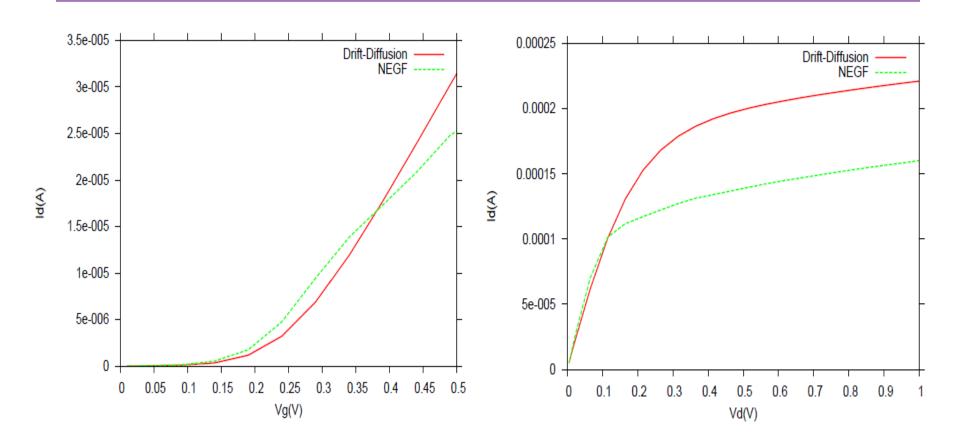
NEGF region electron conc. distribution at Vg=1V Vd=1V





NEGF current flow spectrum at Vg=1V Vd=1V





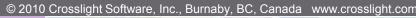
Comparison of DD and NEGF models. Both models used quantum confinement. DD model uses simple bulk mobility.



Summary

- Crosslight's NEGF based simulation tools are suitable for nanowire MOSFET simulation.
- ➤ Hybrid approach combining DD and NEGF offer both accuracy and efficiency.
- ➤ Use of cylindrical coordinate system further enhances computation efficiency.
- For both Id-Vd and Id-Vg curves, total computation time is 7 minutes on an i7 laptop with Windows 7.
- ➤ It was found that without elaborate silicon mobility model calibration, the difference between DD and NEGF can be large.





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